



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



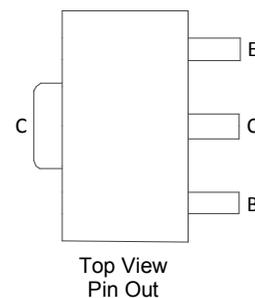
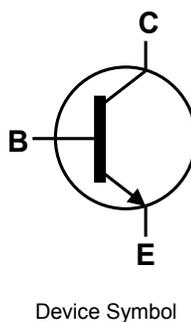
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Features

- $BV_{CEO} = 12V$
- $I_C = 3.0A$ Continuous Current
- Low Saturation Voltage $V_{CE(sat)} < 40mV @ 100mA$
- Complementary PNP Type: NK-FCX789A

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.05 grams (Approximate)



Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	3	A
Peak Pulse Collector Current (single pulse)	I_{CM}	10	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

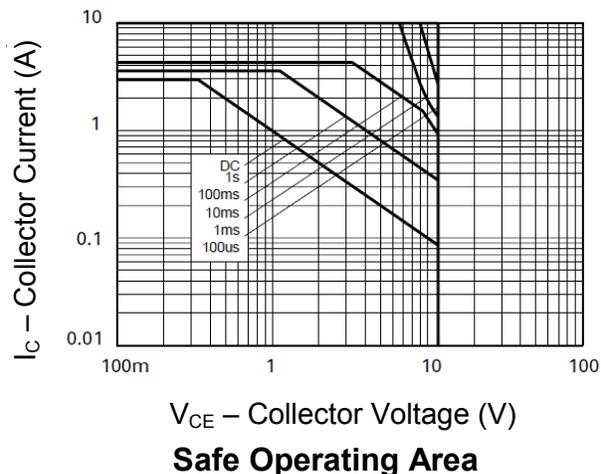
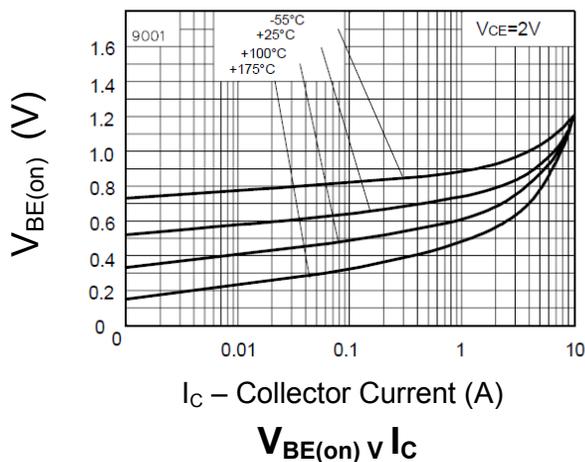
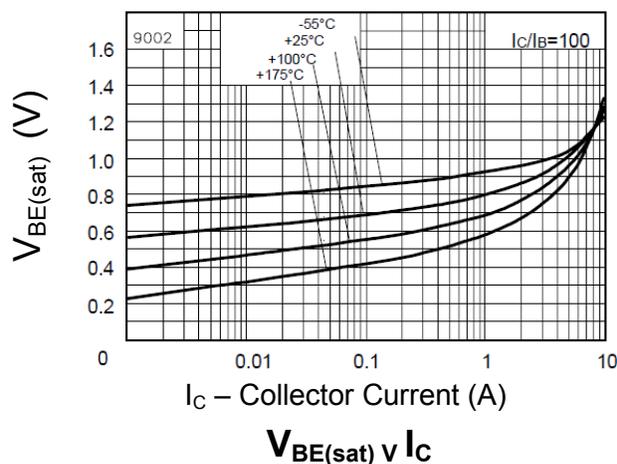
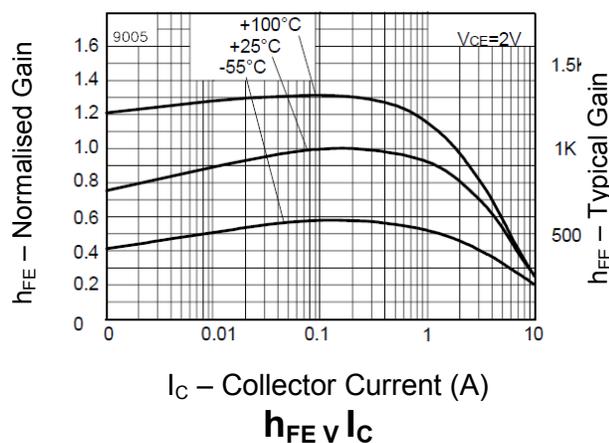
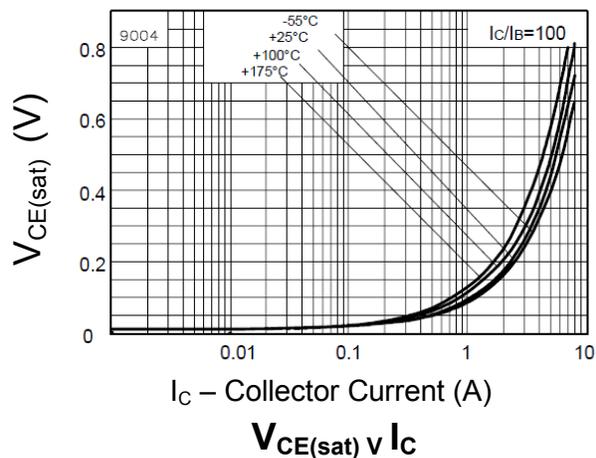
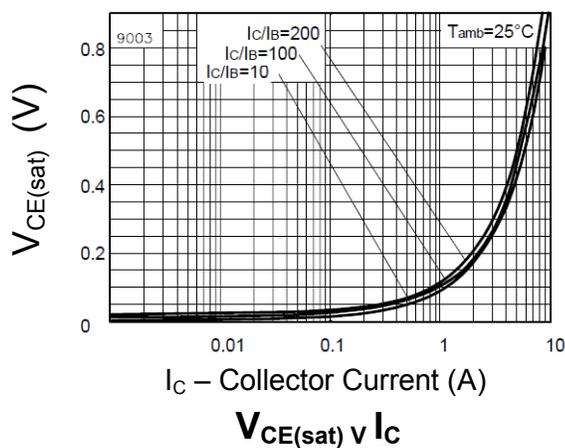
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	1	W
Power Dissipation (Note 6)	P_D	2	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	12	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 7)	BV_{CEO}	12	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 9\text{V}$
Emitter Cut-Off Current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage (Note 7)	$V_{CE(sat)}$	—	—	40 60 180 350 400	mV	$I_C = 0.1\text{A}, I_B = 1\text{mA}$ $I_C = 0.1\text{A}, I_B = 0.5\text{mA}$ $I_C = 1\text{A}, I_B = 10\text{mA}$ $I_C = 3\text{A}, I_B = 10\text{mA}$ $I_C = 4\text{A}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage (Note 7)	$V_{BE(sat)}$	—	—	1.1	mV	$I_C = 3\text{A}, I_B = 20\text{mA}$
Base-Emitter Turn-On Voltage (Note 7)	$V_{BE(on)}$	—	—	1.0	mV	$I_C = 3\text{A}, V_{CE} = 2\text{V}$
DC Current Gain (Note 7)	h_{FE}	500 400 100	—	—	—	$I_C = 100\text{mA}, V_{CE} = 2\text{V}$ $I_C = 3\text{A}, V_{CE} = 2\text{V}$ $I_C = 10\text{A}, V_{CE} = 2\text{V}$
Transitional frequency	f_T	150	—	—	MHz	$I_C = 50\text{mA}, V_{CE} = 5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}	—	200	—	pF	$V_{EB} = 0.5\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{obo}	—	40	—	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Switching Time	t_{on}	—	40	—	ns	$I_C = 500\text{mA}, V_{CC} = 10\text{V},$ $I_{B1} = I_{B2} = 50\text{mA}$
	t_{off}	—	500	—		

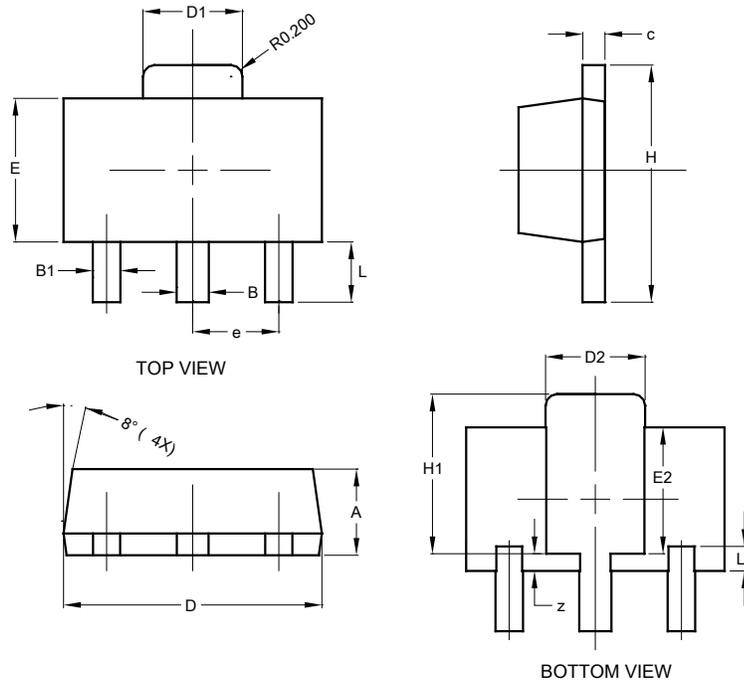
- Notes:
5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.
 6. Same as note (5), except the device is mounted on 40mm x 40mm x 0.6mm single sided 1oz weight copper.
 7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

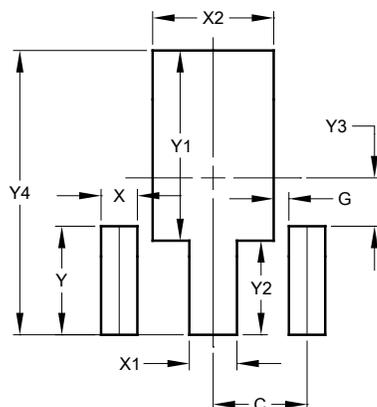
SOT89



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530